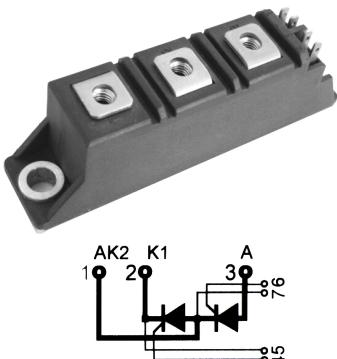


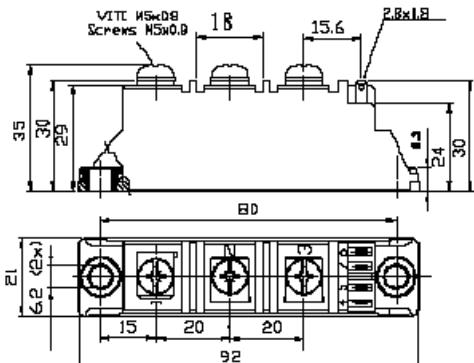
STT60GKxxB

Thyristor-Thyristor Modules



| Type | V _{RSRM} V _{DSTM} | V _{RRM} V _{DRM} |
|------------|--|--------------------------------------|
| | V | V |
| STT60GK08B | 900 | 800 |
| STT60GK12B | 1300 | 1200 |
| STT60GK14B | 1500 | 1400 |
| STT60GK16B | 1700 | 1600 |
| STT60GK18B | 1900 | 1800 |

Tolerance: $\pm 0.5\text{mm}$
Dimensions in mm (1mm=0.0394")



| Symbol | Test Conditions | Maximum Ratings | Unit | |
|--|--|---|------------------|------|
| I _{TRMS} , I _{FRMS} I _{TAVM} , I _{FAVM} | T _{VJ} =T _{VJM} T _G =85°C; 180° sine | 94 60 | A | |
| I _{TSM} , I _{FSM} | T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine | 1500 1600 | A | |
| | T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine | 1350 1450 | | |
| i ² dt | T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine | 11200 10750 | A ² s | |
| | T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine | 9100 8830 | | |
| (di/dt) _{cr} | T _{VJ} =T _{VJM} f=50Hz, t _p =200us V _D =2/3V _{DRM} I _G =0.45A di/dt=0.45A/us | repetitive, I _T =150A non repetitive, I _T =I _{TAVM} | 150 500 | A/us |
| (dv/dt) _{cr} | T _{VJ} =T _{VJM} ; V _{DR} =2/3V _{DRM} R _{GK} = ∞ ; method 1 (linear voltage rise) | 1000 | V/us | |
| P _{GM} | T _{VJ} =T _{VJM} I _T =I _{TAVM} | t _p =30us t _p =300us | 10 5 | W |
| P _{GAV} | | | 0.5 | W |
| V _{RGM} | | | 10 | V |
| T _{VJ} T _{VJM} T _{stg} | | -40...+125 125 -40...+125 | °C | |
| V _{ISOL} | 50/60Hz, RMS I _{ISOL} \leq 1mA | t=1min t=1s | 3000 3600 | V~ |
| M _d | Mounting torque (M5) Terminal connection torque (M5) | 2.5-4.0/22-35 2.5-4.0/22-35 | Nm/lb.in. | |
| Weight | Typ. | 110 | g | |

Sirecifier®

STT60GKxxB

Thyristor-Thyristor Modules

| Symbol | Test Conditions | Characteristic Values | Unit |
|--------------------|---|-----------------------|-----------|
| I_{RRM}, I_{DRM} | $T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$ | 5 | mA |
| V_{TM} | $I_{TM}=180A; T_{VJ}=25^\circ C$ | 1.65 | V |
| V_{TO} | For power-loss calculations only ($T_{VJ}=125^\circ C$) | 0.85 | V |
| r_T | | 3.7 | $m\Omega$ |
| V_{GT} | $V_D=6V; T_{VJ}=25^\circ C$ $T_{VJ}=-40^\circ C$ | 1.5 max 1.6 max | V |
| I_{GT} | $V_D=6V; T_{VJ}=25^\circ C$ $T_{VJ}=-40^\circ C$ | 100 200 | mA |
| V_{GD} | $T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$ | 0.2 | V |
| I_{GD} | | 10 | mA |
| I_L | $T_{VJ}=25^\circ C; t_p=10\mu s; V_D=6V$ $I_G=0.45A; dI/dt=0.45A/\mu s$ | 450 | mA |
| I_H | $T_{VJ}=25^\circ C; V_D=6V; R_{GK}=\infty$ | 200 | mA |
| t_{gd} | $T_{VJ}=25^\circ C; V_D=1/2V_{DRM}$ $I_G=0.45A; dI/dt=0.45A/\mu s$ | 2 | us |
| t_q | $T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -dI/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ | typ. 150 | us |
| Q_s | $T_{VJ}=T_{VJM}; I_T, I_F=50A; -dI/dt=3A/\mu s$ | 100 | uC |
| I_{RM} | | 24 | A |
| R_{thJC} | per thyristor/diode; DC current per module | 0.45 0.225 | K/W |
| R_{thJK} | per thyristor/diode; DC current per module | 0.65 0.325 | K/W |
| ds | Creeping distance on surface | 12.7 | mm |
| da | Strike distance through air | 9.6 | mm |
| a | Maximum allowable acceleration | 50 | m/s^2 |

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHs compliant

APPLICATIONS

- * DC motor control
- * Softstart AC motor controller
- * Light, heat and temperature control

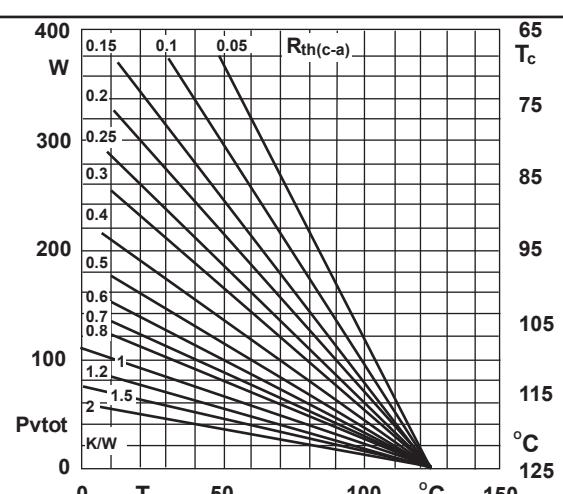
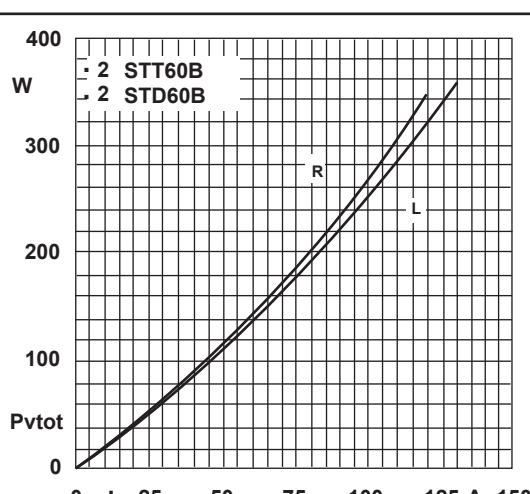
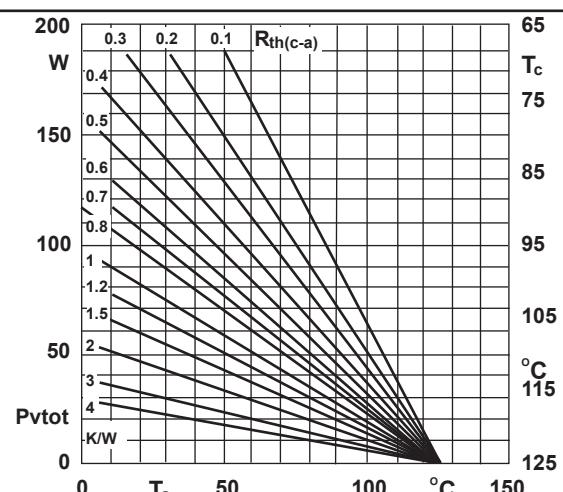
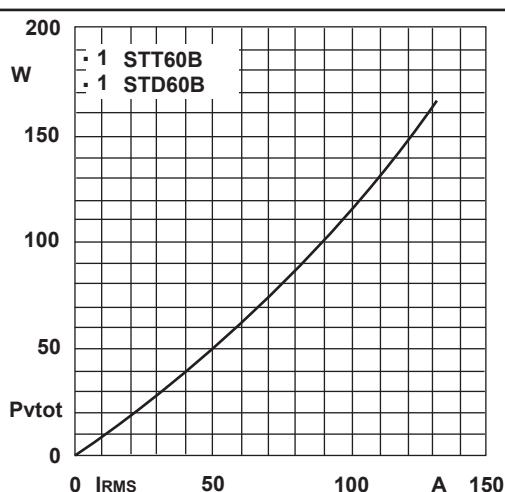
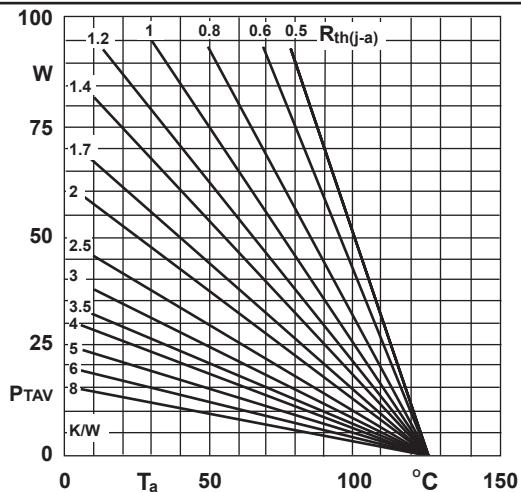
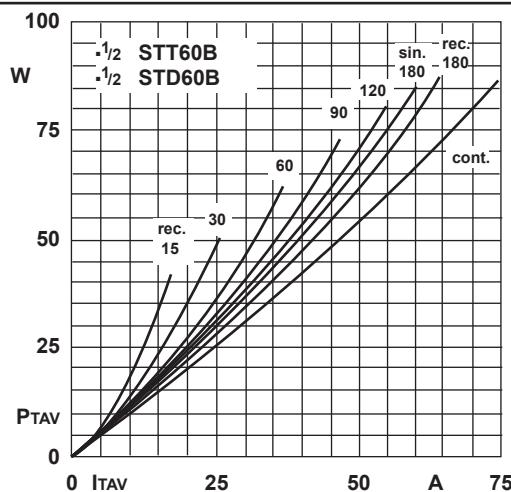
ADVANTAGES

- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits

Sirectifier®

STT60GKxxB

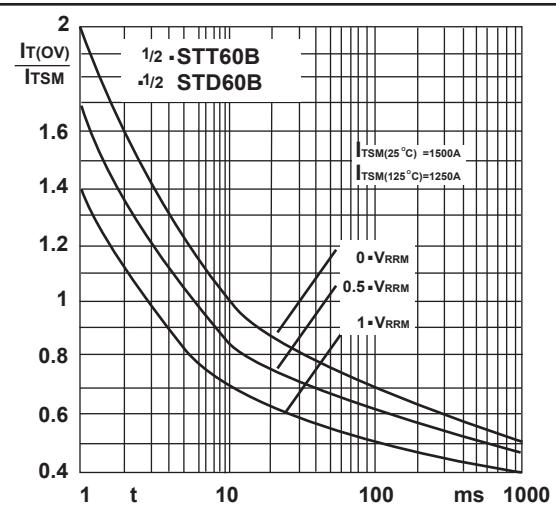
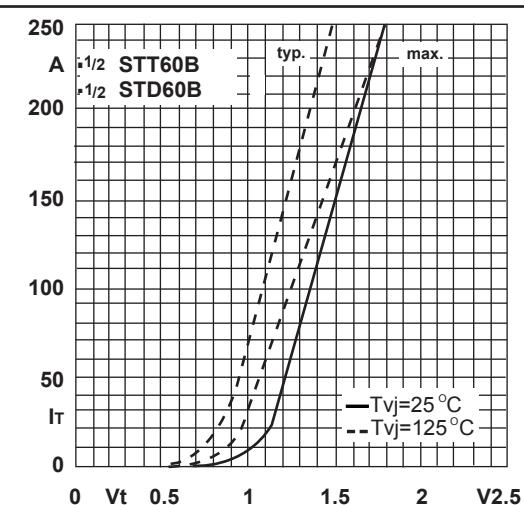
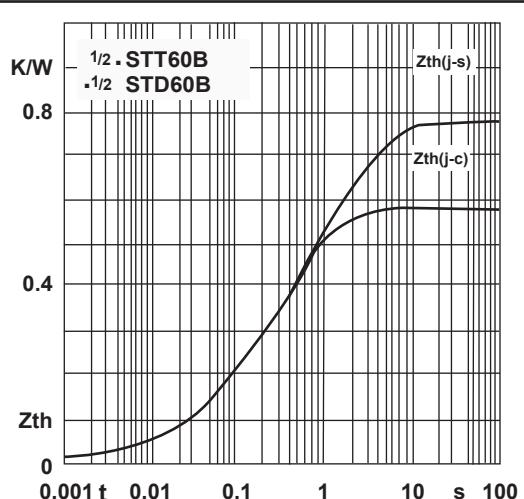
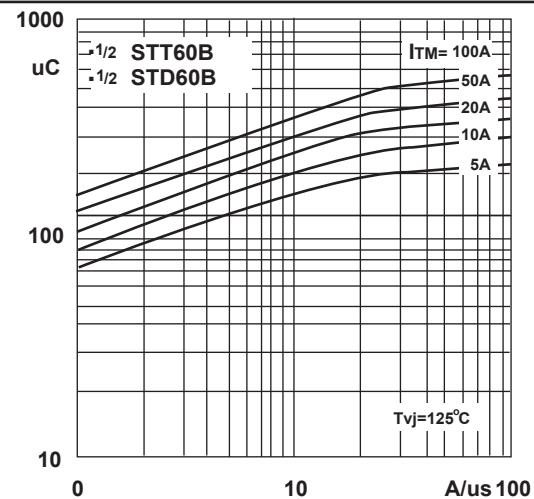
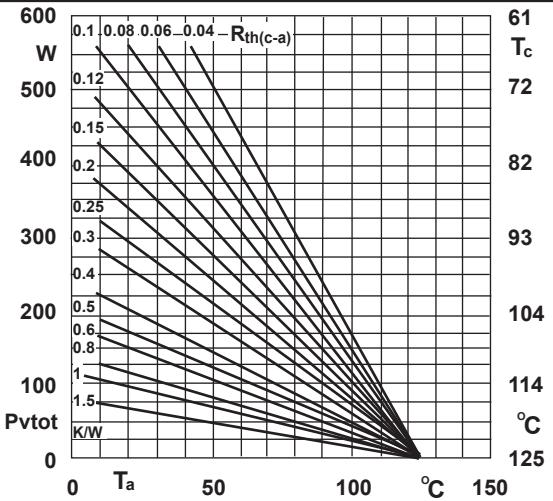
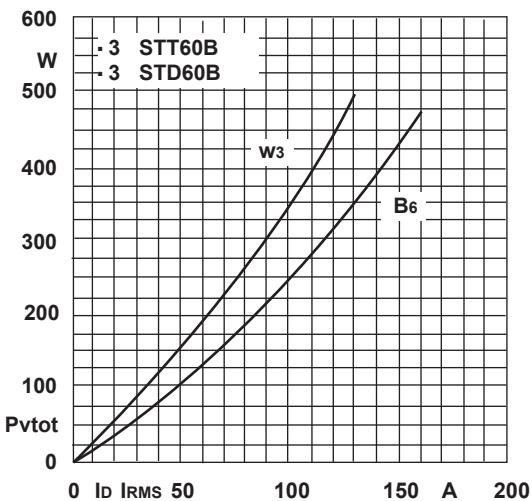
Thyristor-Thyristor Modules



Sirectifier®

STT60GKxxB

Thyristor-Thyristor Modules



Sirecifier®